IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application No.:	10/797,972	Filing Date:	March 10, 2004
Confirmation No.:	Unassigned		
First Named Inventor:	Yi Ding		
Assignee:	ProMOS Technologies, Inc.		
Examiner:	Unassigned	Art Unit:	Unassigned
Attorney Docket No.:	M-15297 US		

San Jose, California
April 16, 2004

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT UNDER 37 CFR § 1.97(b)

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Pursuant to 37 CFR § 1.56, § 1.97 and § 1.98, the documents listed on the accompanying form PTO-1449 are called to the attention of the Examiner for the above patent application. Copies of these documents are enclosed except for United States Patents and United States Published Patent Applications.

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Michael Shenker 4-16-04

Attorney for Applicant(s) Date of Signature

Respectfully submitted,

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U.S. Department of Commerce, Patent and Trademark Office	Atty Docket No.	Serial No.
	M-15297 US	10/797,972
INFORMATION DISCLOSURE STATEMENT BY APPLICANT	Applicant(s)	
(Use several sheets if necessary)	Yi Ding	
	Filing Date	Group
	March 10, 2004	Unassigned

U.S. Patent Documents

*Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date If Appropriate
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	AB	5,856,943	5 Jan. 1999	Jenq			
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	AD	6,057,575	2 May 2000	Jenq			
	AE	6,130,129	10 Oct. 2000	Chen			
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Examiner	Date Considered

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	AZ	Wu, A.T.; Chan T.Y.; Ko, P.K.; and Hu, C. "A Novel High-Speed, 5-Volt Programming EPROM Structure With Source-Side Injection," 1986 IEEE, 584-587.
	BA	Mizutani, Yoshihisa; and Makita, Koji "A New EPROM Cell With A Sidewall Floating Gate Fro High-Density and High Performance Device," 1985 IEEE, 635-638.
	BB	Ma, Y.; Pang, C.S.; Pathak, J.; Tsao, S.C.; Chang, C.F.; Yamauchi, Y.; Yoshimi, M. "A Novel High Density Contactless Flash Memory Array Using Split-Gate Source-Side-Injection Cell for 5V-Only Applications," 1994 Symposium on VLSI Technology Digest of Technical Papers, pages 49-50.
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	BD	Ma, Yale et al., "A Dual-Bit Split-Gate EEPROM (DSG) Cell in Contactless Array for Single Vcc High Density Flash Memories," 1994 IEEE, 3.5.1-3.5.4.
	BE	Spinelli, Alessandro S., "Quantum-Mechanical 2D Simulation of Surface-and Buried-Channel p-MOS,"2000 International Conference on Simulation of Semiconductor Processes and Devices: SISPAD 2000, Seattle, WA September 6-8, 2000
	BF	Kim, K.S. et al. "A Novel Dual String NOR (DuSnor) Memory Cell Technolgy Scalabe to the 256 Mbit and 1 Gbit Flash Memories," 1995 IEEE 11.1.1-11.1.4
	BG	Bergemont, A. et al."NOR Virtual Ground (NVG)- A New Scaling Concept for Very High Density FLAS EEPROM and its Implementation in a 0.5 um Process," 1993 IEEE 2.2.1-2.2.4
	BH	Van Duuren, Michiel et al., "Compact poly-CMP Embedded Flash Memory Cells For One or Two Bit Storage," Philips Research Leuven, Kapeldreef 75, B3001 Leuven, Belgium, pages 73-74.
	BI	United States Patent Application No. 10/440,466, entitled "Fabrication Of Conductive Gates For Nonvolatile Memories From Layers With Protruding Portions," Filed on May 16, 2003; Attorney Docket No.: M-12979 US.
	BJ	United States Patent Application No. 10/440,005, entitled "Fabrication of Dielectric On A Gate Surface To Insulate The Gate From Another Element Of An Integrated Circuit," Filed on May 16, 2003; Attorney Docket No.: M-15203 US.
	BK	United States Patent Application No. 10/440,508, entitled "Fabrication Of Gate Dielectric In Nonvolatile Memories Having Select, Floating And Control Gates," Filed on May 16, 2003; Attorney Docket No.: M-15204 US.
	BL	United States Patent Application No. 10/440,500, entitled "Integrated Circuits With Openings that Allow Electrical Contact To Conductive Features Having Self-Aligned Edges," Filed on May 16, 2003; Attorney Docket No.: M-15205 US.
	BM	United States Patent Application No. 10/393,212, entitled "Nonvolatile Memories And Methods Of Fabrication," Filed on March 19, 2003; Attorney Docket No.: M-12902 US.

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OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)		
	BN	United States Patent Application No. 10/411,813, entitled "Nonvolatile Memories With A Floating Gate Having An Upward Protrusion," Filed on April 10, 2003; Attorney Docket No.: M-12903 US.
	BO	United States Patent Application No. 10/393,202, entitled "Fabrication of Integrated Circuit Elements In Structures With Protruding Features," Filed on March 19, 2003; Attorney Docket No.: M-15151 US.
	BP	United States Patent Application No. 10/631,941, entitled "Nonvolatile Memory Cell With Multiple Floating Gates Formed After The Select Gate," Filed on July 30, 2003; Attorney Docket No.: M-15171 US.
	BQ	United States Patent Application No. 10/632,155, entitled "Nonvolatile Memory Cells With Buried Channel Transistors," Filed on July 30, 2003; Attorney Docket No.: M-15222 US.
	BR	United States Patent Application No. 10/632,007, entitled "Arrays Of Nonvolatile Memory Cells Wherin Each Cell Has Two Conductive Floating Gates," Filed on July 30, 2003; Attorney Docket No.: M-15223 US.
	BS	United States Patent Application No. 10/631,452, entitled "Fabrication Of Dielectric For A Nonvolatile Memory Cell Having Multiple Floating Gates," Filed on July 30, 2003; Attorney Docket No.: M-15229 US.
	BT	United States Patent Application No. 10/632,154, entitled "Fabrication Of Gate Dielectric In Nonvolatile Memories In Which A Memory Cell Has Mutiple Floating Gates," Filed on July 30, 2003; Attorney Docket No.: M-15230 US.
	BU	United States Patent Application No. 10/632,186, entitled "Nonvolatile Memory Cell With Multiple Floating Gates Formed After The Select Gate And Having Upward Protrusions," Filed on July 30, 2003; Attorney Docket No.: M-15241 US.
	BV	United States Patent Application No. 10/631,552, entitled "Nonvolatile Memories And Methods Of Fabrication," Filed on July 30, 2003; Attorney Docket No.: M-12902-1P US.
	BW	Shirota, Riichiro "A Review of 256Mbit NAND Flash Memories and NAND Flash Future Trend," February 2000, Nonvolatile Memory Workshop in Monterey, California, pages 22-31.
	BX	United States Patent Application No. 10/798,475, entitled "Fabrication Of Conductived Lines Interconnecting Conductive Gates In Nonvolatile Memories And Non-Volatile Memory Structures," Filed on March 10, 2004; Attorney Docket No.: M-15296 US.

Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
	BY	EP 0 938 098 A2	25 Aug. 1999	Europe				

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